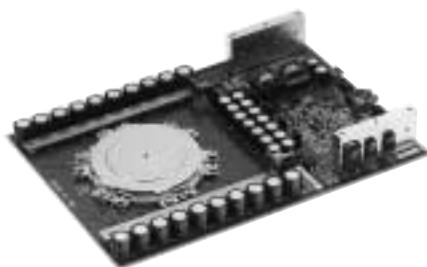


GCU15CA-130HIGH POWER INVERTER USE
PRESS PACK TYPE**GCU15CA-130**

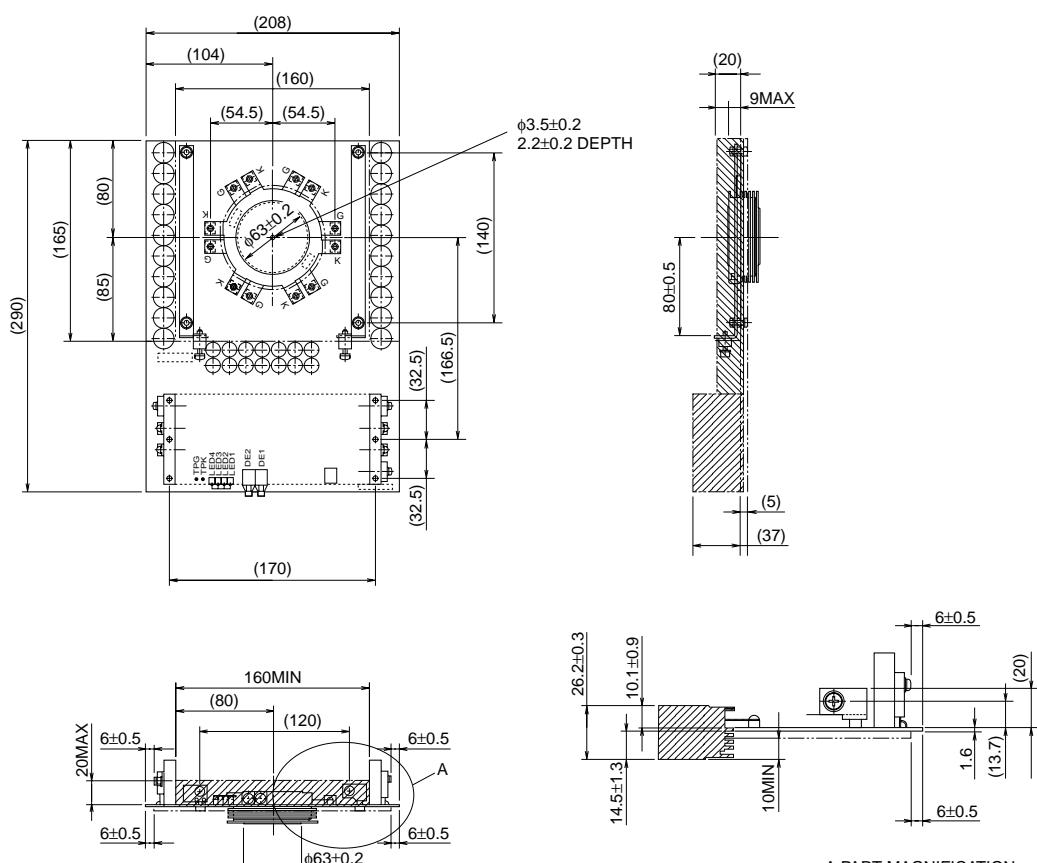
- Symmetrical GCT unit
- GCT and gate driver are connected
- ITQRM Repetitive controllable on-state current 1500A
- IT(AV): Average on-state current 500A
- VDRM: Repetitive peak off-state voltage 6500V
- VRM: Repetitive peak reverse voltage 6500V
- T_j: Operation junction temperature 125°C

APPLICATION

Current source inverters, DC choppers, Induction heaters, DC to DC converter

OUTLINE DRAWING

Dimensions in mm



A PART MAGNIFICATION

GCT PART**MAXIMUM RATINGS**

Symbol	Parameter	Conditions	Voltage class	Unit
VRRM	Repetitive peak reverse voltage	—	6500	V
VRSM	Non-repetitive peak reverse voltage	—	6500	V
VDRM	Repetitive peak off-state voltage	Gate driver energized	6500	V
VDSC	Non-repetitive peak off-state voltage	Gate driver energized	6500	V
V(LTDS)	Long term DC stability voltage	Gate driver energized, $\lambda = 100$ Fit	3600	V

Symbol	Parameter	Conditions	Ratings	Unit
IT(RMS)	RMS on-state current	Applied for all condition angles	780	A
IT(AV)	Average on-state current	f = 60Hz, sinewave $\theta = 180^\circ$, Tf = 66°C	500	A
ITQRM	Repetitive controllable on-state current	VDM = 3/4 VDRM, VD = 3000V, LC = 0.3μH Tj = 25/125°C (See Fig. 1, 3)	1500	A
ITSM	Surge on-state current	One half cycle at 60Hz, Tj = 125°C start	8	kA
I ² t	Current-squared, time integration	VD = 3000V, IT = 1500A, Cs = 0.2μF, RS = 5Ω Tj = 25/125°C, f = 60Hz (See Fig. 1, 2)	2.7×10^5	A ² s
dIT/dt	Critical rate of rise of on-state current	VD = 3000V, IT = 1500A, Cs = 0.2μF, RS = 5Ω Tj = 25/125°C, f = 60Hz (See Fig. 1, 2)	1000	A/μs
dIR/dt	Critical rate of rise of reverse recovery current	IT = 1500A, VR = 3000V, Tj = 25/125°C Cs = 0.2μF, RS = 5Ω (See Fig. 4, 5)	1000	A/μs
PFGM	Peak forward gate power dissipation		9	kW
PRGM	Peak reverse gate power dissipation		32	kW
PFG(AV)	Average forward gate power dissipation		180	W
PRG(AV)	Average reverse gate power dissipation		230	W
VFGM	Peak forward gate voltage		10	V
VRGM	Peak reverse gate voltage		21	V
IFGM	Peak forward gate current		900	A
IRGM	Peak reverse gate current		1500	A

ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	Limits			Unit
			Min	Typ	Max	
VTM	On-state voltage	IT = 800A, Tj = 125°C	—	—	6	V
IRRM	Repetitive peak reverse current	VRM = 6500V, Tj = 125°C	—	—	300	mA
IDRM	Repetitive peak off-state current	VDM = 6500V, Tj = 125°C, Gate driver energized	—	—	150	mA
IGRM	Reverse gate current	VRG = 21V, Tj = 125°C	—	—	100	mA
dv/dt	Critical rate of rise of off-state voltage	VD = 3000V, Tj = 125°C Gate driver energized (Expo. wave)	3000	—	—	V/μs
tgt	Turn-on time	IT = 1500A, VD = 3000V, di/dt = 1000A/μs, Tj = 125°C	—	—	5	μs
td	Turn-on delay time	CS = 0.2μF, RS = 5Ω (See Fig. 1, 2)	—	—	1	μs
Eon	Turn-on switching energy	IT = 800A, VD = 3000V, di/dt = 1000A/μs CS = 0.2μF, RS = 5Ω, Tj = 125°C (See Fig. 1, 2)	—	—	1.3	J/P
ts	Storage time	IT = 1500A, VDM = 3/4 VDRM, VD = 3000V CS = 0.2μF, RS = 5Ω, Tj = 125°C (See Fig. 1, 5)	—	—	3	μs
Eoff	Turn-off switching energy	IT = 800A, VDM = 4000V, VD = 3000V CS = 0.2μF, RS = 5Ω, Tj = 125°C (See Fig. 1, 5)	—	—	5.2	J/P
QRR	Reverse recovery charge	VR = 3000V, IT = 800A, di/dt = 1000A/μs	—	—	2000	μC
Erec	Reverse recovery energy	CS = 0.2μF, RS = 5Ω, Tj = 125°C (See Fig. 4, 5)	—	—	7.4	J/P
IGT	Gate trigger current	VD = 24V, RL = 0.1Ω, Tj = 25°C	—	—	0.75	A
VGT	Gate trigger voltage	DC method	—	—	1.5	V

MITSUBISHI GCT (Gate Commutated Turn-off) THYRISTOR UNIT

GCU15CA-130

**HIGH POWER INVERTER USE
PRESS PACK TYPE**

GATE DRIVER PART

Symbol	Parameter	Conditions	Limits			Unit
			Min	Typ	Max	
VGIN	Power supply voltage	DC power supply	19	20	21	V
PGIN	Gate power consumption	I _T = 830Arms, f = 780Hz, duty = 0.33	—	—	50	W
t _{fd}	Delay time of on gate current	T _a = 25°C	—	—	3.0	μs
t _{rd}	Delay time of off gate current	T _a = 25°C	—	—	3.0	μs
—	Control signal	Optical fiber data link Transmitter : HFBR-1521 : Agilent Receiver : HFBR-2521 : Agilent	—	—	—	—
—	Power supply connector	Phoenix contact Type name : MSTB25/2-G-508AU	—	—	—	—
—	Status signal	—	(Note 1)		—	—

MECHANICAL DATA

Symbol	Parameter	Conditions	Limits			Unit
			Min	Typ	Max	
F _M	Mounting force	—	18	20	24	kN
—	Weight	—	—	1560	—	g
—	Pole piece diameter (GTC device)	±0.2mm	—	63	—	mm
—	Housing thickness (GTC device)	±0.5mm	—	26	—	mm

THERMAL DATA

Symbol	Parameter	Conditions	Limits			Unit
			Min	Typ	Max	
T _j	Junction operating temperature	—	-10	—	125	°C
T _{stg}	Storage temperature	—	-10	—	60	°C
T _a	Ambient operation temperature	Recommend : ≤ 40°C	-10	—	60	°C
R _{t(j-f)}	Thermal resistance	Junction to Fin	—	—	0.014	K/W

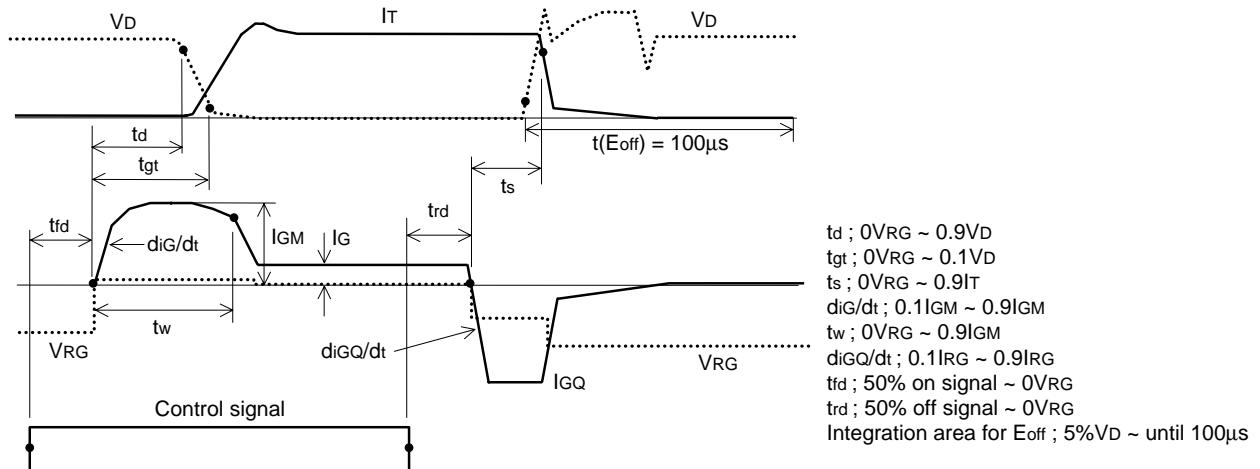


Fig. 1 Turn-on and Turn-off waveform

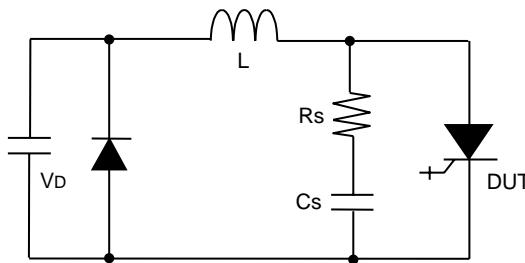


Fig. 2 Turn-on test circuit

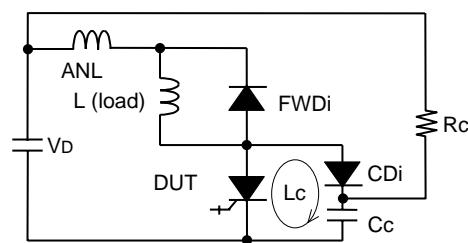
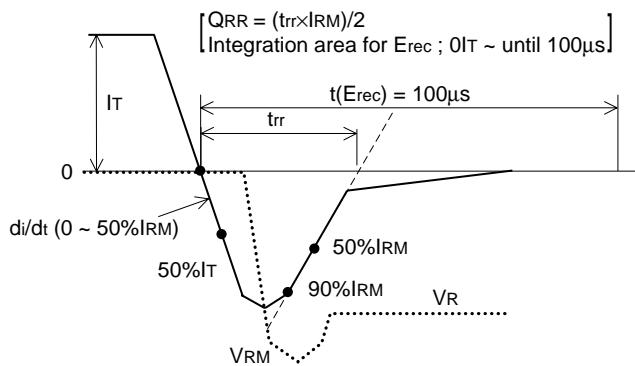
Fig. 3 Turn-off test circuit
(With clamp circuit)

Fig. 4 Reverse recovery waveform

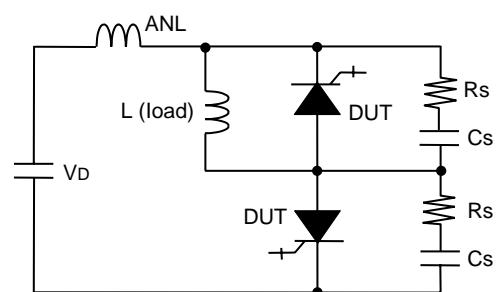


Fig. 5 Turn-off and Reverse recovery test circuit

Note 1. Status signal

1. Status signal from LED

(1) Status signal

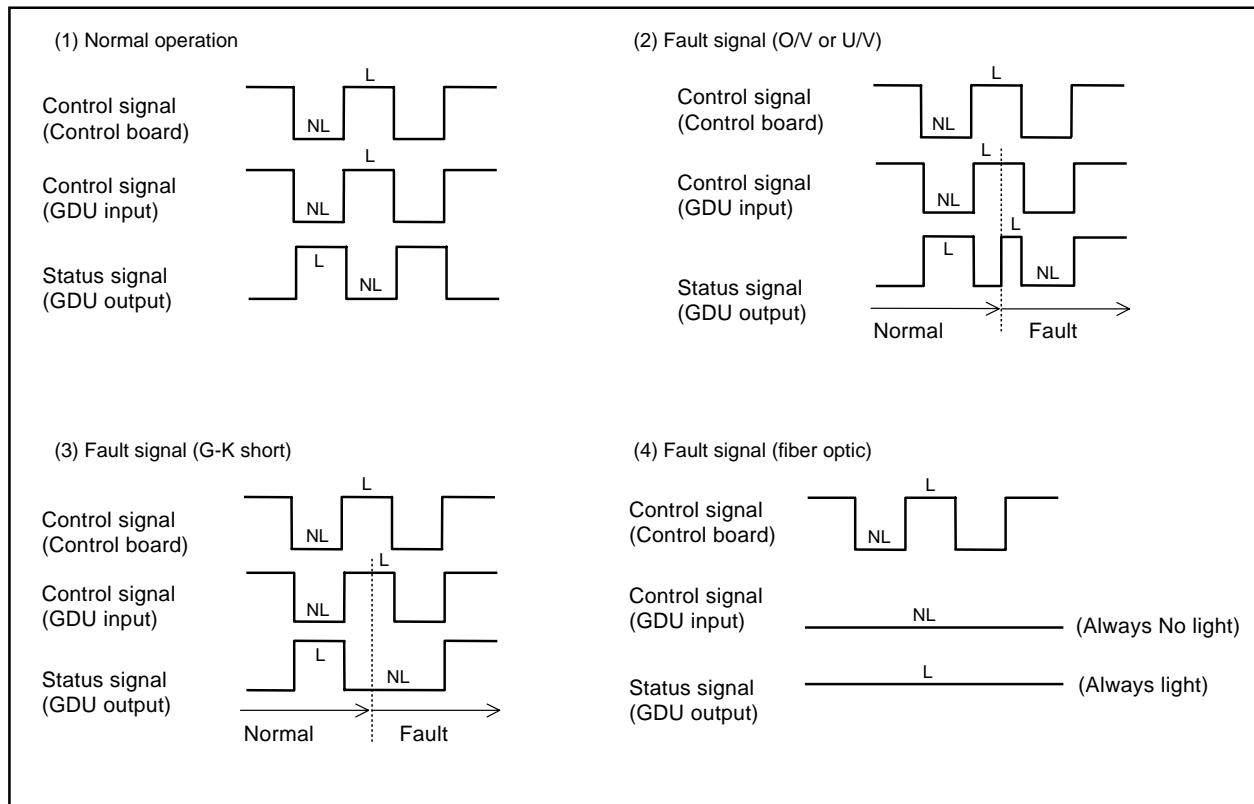
Status of GCT	LED 1 (Red)	LED 2 (Yellow)
On state	OFF	ON
Off state	ON	OFF

(2) Fault signal

Status	G-K	Power Supply	G-K LED (LED 3) (Green)	PS LED (LED 4) (Green)
Normal	Normal	20±1V	On	On
Fault	Normal	Voltage down	Off	Off
Fault	G-K short	20±1V	Off	On
Fault	G-K short	Voltage down	Off	Off

2. Status signal from Transmitter

(L : Light NL : No light)



MITSUBISHI GCT (Gate Commutated Turn-off) THYRISTOR UNIT

GCU15CA-130

HIGH POWER INVERTER USE
PRESS PACK TYPE

Note 2. Additional support for vibration test

Additional support is necessary for vibration test of GCU15CA-130.

Fig. 6 shows detailed figure about connection method between gate driver and heat sink by additional support.

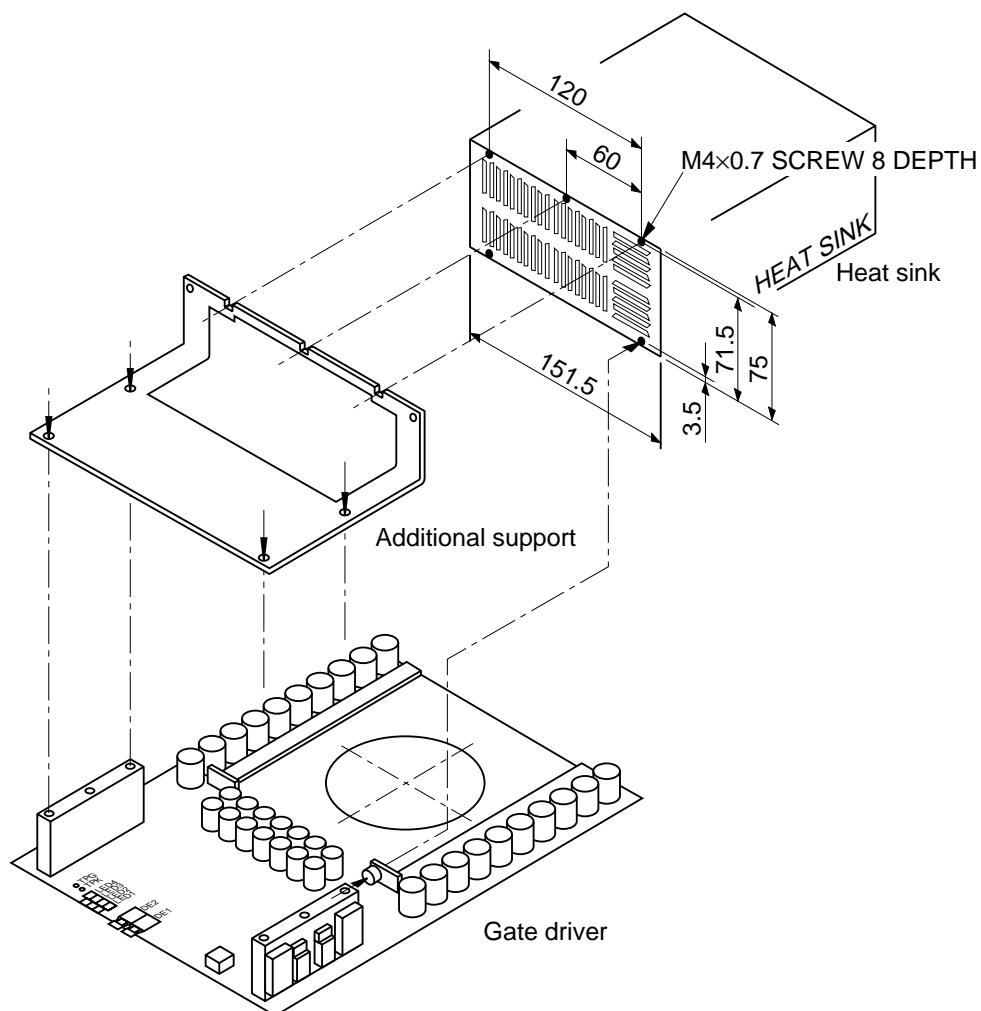
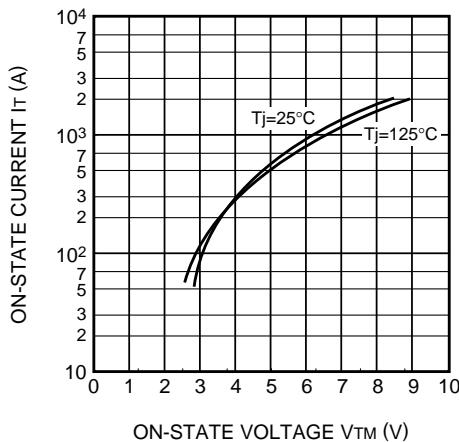
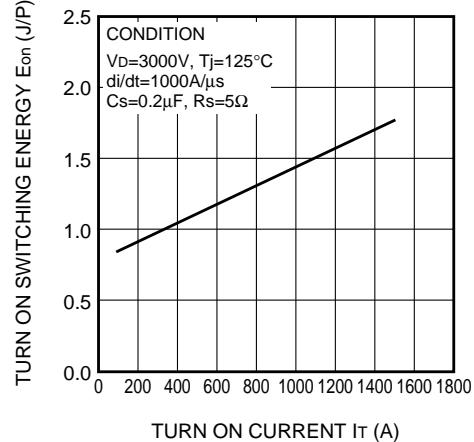
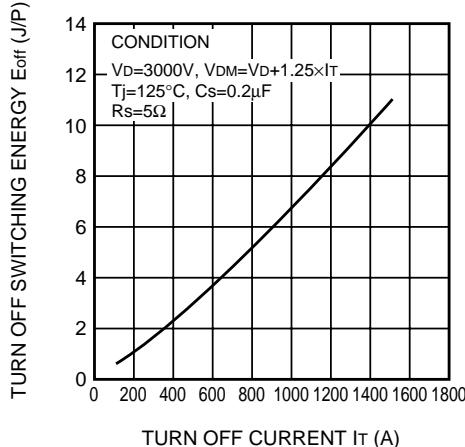
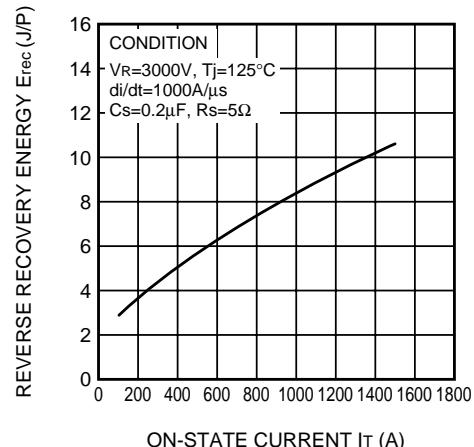


Fig. 6 Connection method between gate driver and heat sink by additional support

PERFORMANCE CURVES**MAXIMUM ON-STATE CHARACTERISTIC** **E_{on} VS I_T (Max)** **E_{off} VS I_T (Max)** **E_{rec} VS I_T (Max)****MAXIMUM THERMAL IMPEDANCE
CHARACTERISTIC
(JUNCTION TO FIN)**